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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK975

Silicon N-Channel MOS FET

RENESAS_x

ADE-208-1243 (Z)
1st. Edition
Mar. 2001

Application

High speed power switching

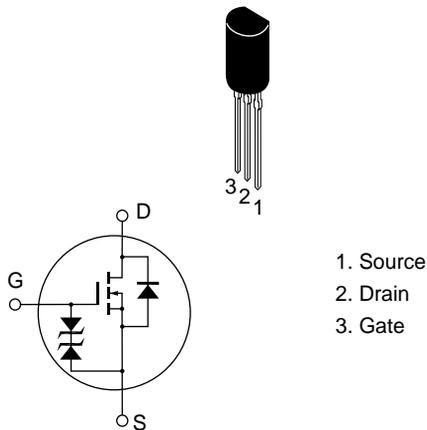
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Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline

TO-92 Mod



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	1.5	A
Drain peak current	$I_{D(pulse)}^{*1}$	4.5	A
Body to drain diode reverse drain current	I_{DR}	1.5	A
Channel dissipation	Pch	900	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

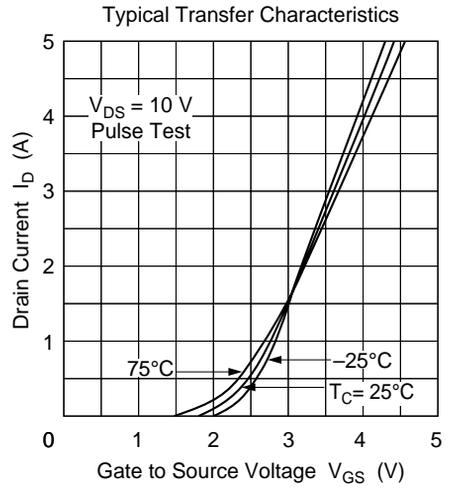
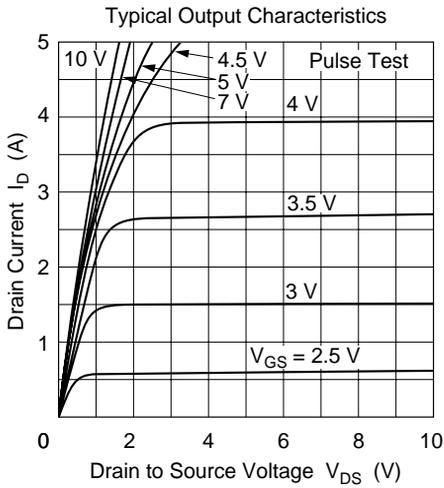
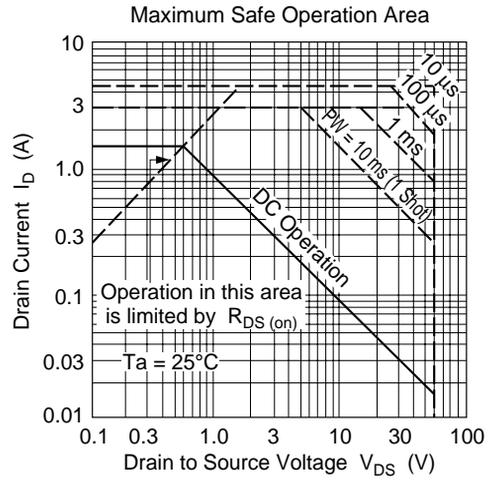
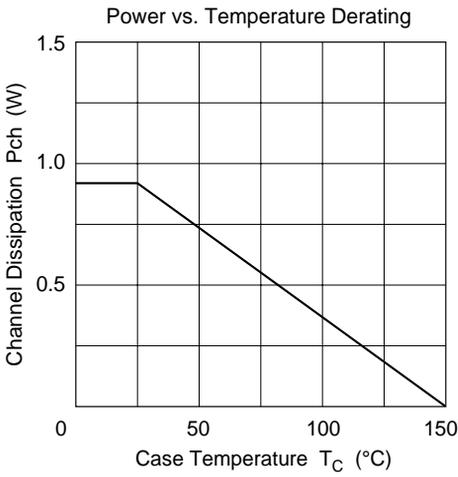
Note: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

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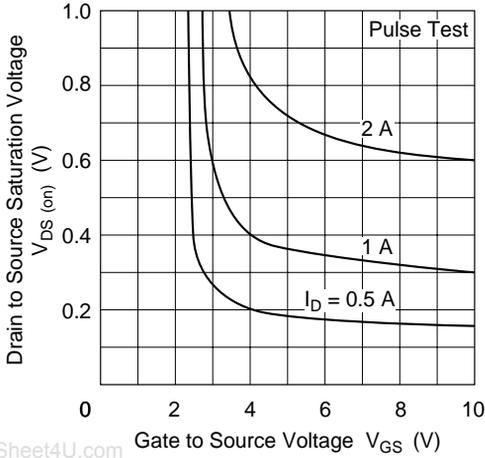
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	100	μA	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(off)}$	—	0.3	0.4	Ω	$I_D = 1 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
			0.4	0.55	Ω	$I_D = 1 \text{ A}$, $V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	yfs	0.9	1.5	—	S	$I_D = 1 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	140	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$,
Output capacitance	C_{oss}	—	70	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	20	—	pF	
Turn-on delay time	$t_{d(on)}$	—	3	—	ns	$I_D = 1 \text{ A}$, $V_{GS} = 10 \text{ V}$,
Rise time	t_r	—	12	—	ns	$R_L = 30 \Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	
Fall time	t_f	—	30	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 1.5 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	45	—	ns	$I_F = 1.5 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$

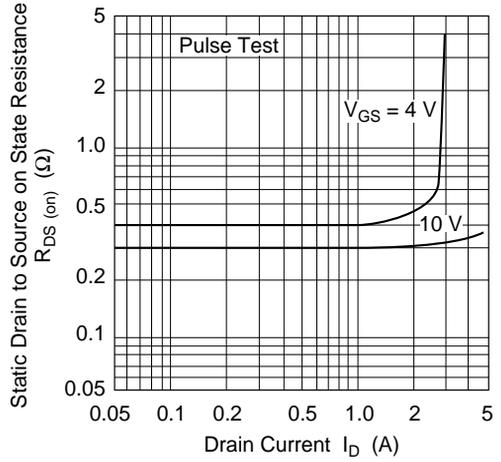
Note: 1. Pulse test



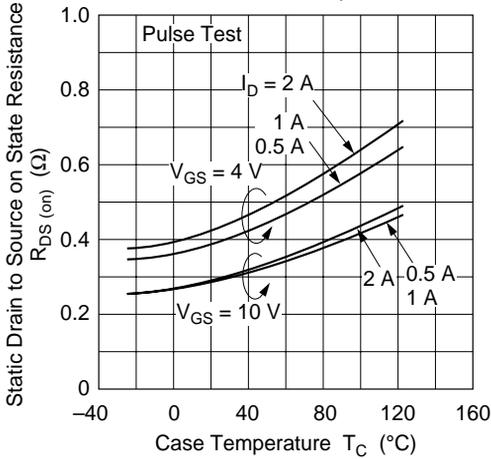
Drain to Source Saturation Voltage vs. Gate to Source Voltage



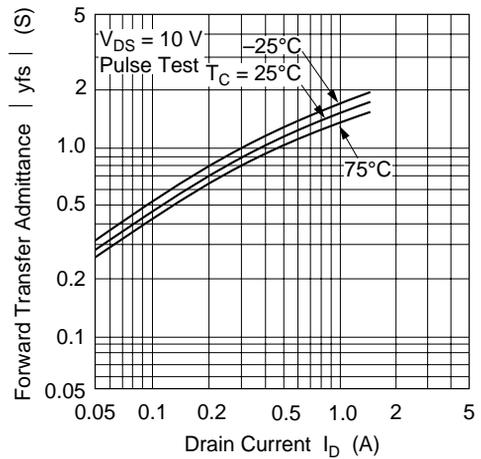
Static Drain to Source On State Resistance vs. Drain Current



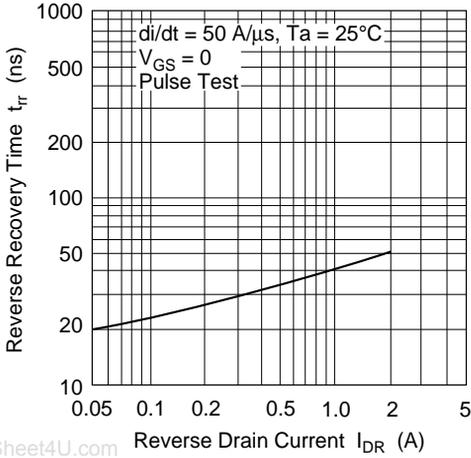
Static Drain to Source on State Resistance vs. Temperature



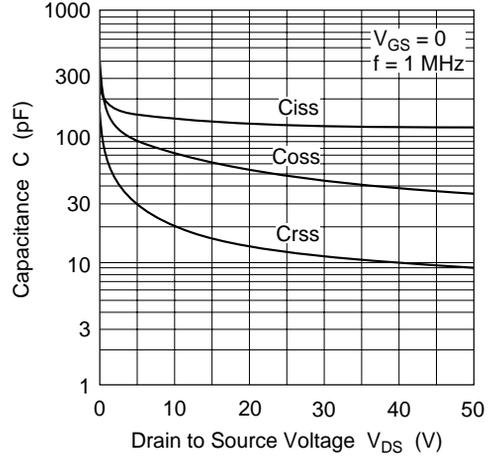
Forward Transfer Admittance vs. Drain Current



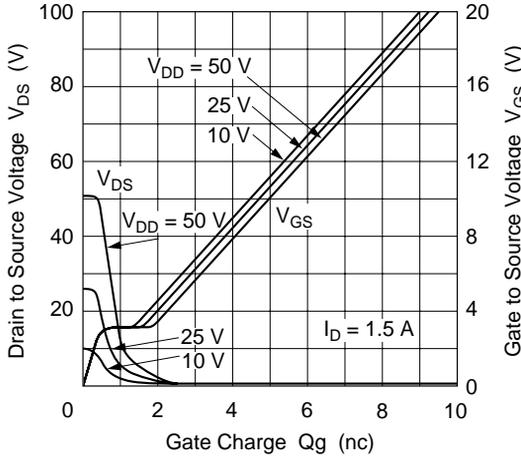
Body to Drain Diode Reverse Recovery Time



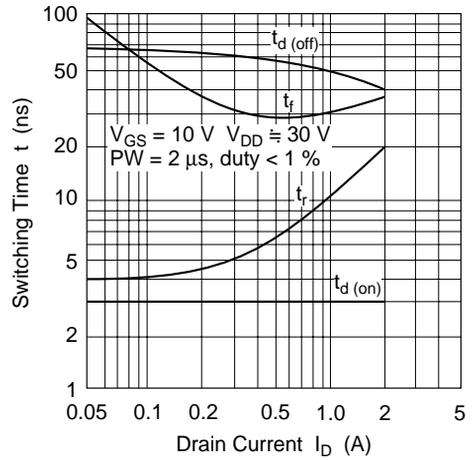
Typical Capacitance vs. Drain to Source Voltage

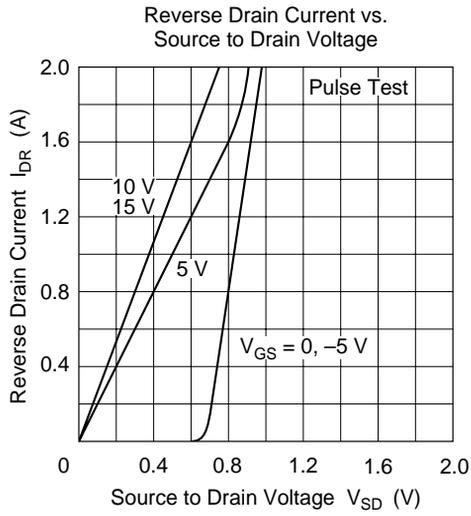


Dynamic Input Characteristics



Switching Characteristics

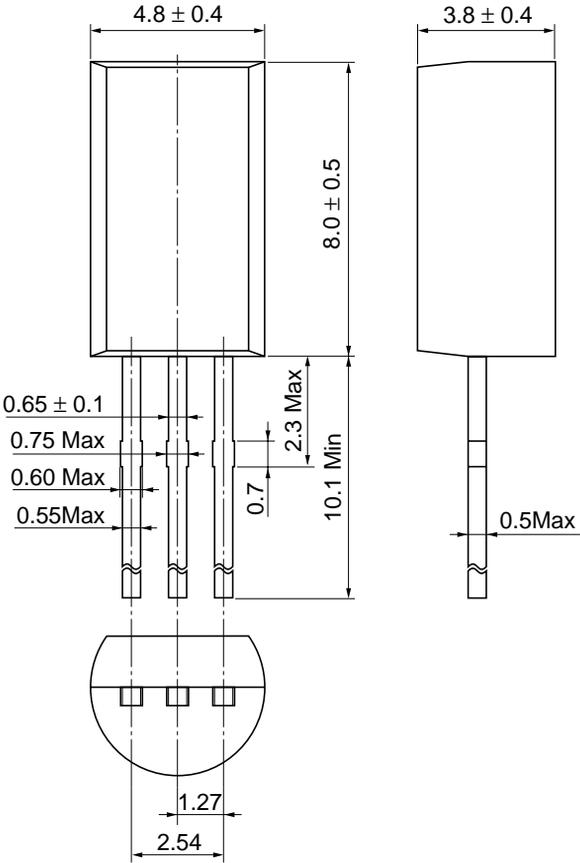




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Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.35 g

Cautions

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